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Fairchild Semiconductor FMMT449

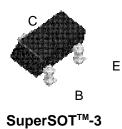
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FMMT449



NPN Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous. Sourced from Process NB.

Absolute Maximum Ratings* T_{A = 25°C unless otherwise noted}

Symbol	Parameter	FMMT449	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous - Peak Pulse Current	1 2	А
T _{J,} T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics $T_{A=25^{\circ}\text{C unless otherwise noted}}$

Symbol	Characteristic	Max	Units		
		FMMT449			
P _D	Total Device Dissipation* Derate above 25°C	500 4	mW mW/°C		
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W		
*Device mounted on FR-4 PCB 4.5" X 5"; mounting pad 0.02 in ² of 2oz copper.					

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NPN Low Saturation Transistor

(continued)

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	30		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1mA	50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40 V V _{CB} = 40 V, Ta=100°C		100 10	nA uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
ON CHAR	ACTERISTICS*				1
h _{FE}	DC Current Gain	$I_C = 50 \text{ mA}, V_{CE} = 2V$	70		-
		$I_C = 500 \text{ mA}, V_{CE} = 2V$	100	300	
		$I_C = 1A$, $V_{CE} = 2V$	80		
		$I_C = 2A$, $V_{CE} = 2V$	40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		500	mV
()		I _C = 2 A, I _B = 200 mA		1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V
SMALL SI	IGNAL CHARACTERISTICS				
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		15	pF
f _T	Transition Frequency	$I_C = 50 \text{mA}, V_{CE} = 10 \text{ V}, f=100 \text{MHz}$	150		MHz
		•			

*Pulse Test: Pulse Width $\leq 300~\mu s,$ Duty Cycle $\leq 2.0\%$



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